

KSA1175**PNP EPITAXIAL SILICON TRANSISTOR**

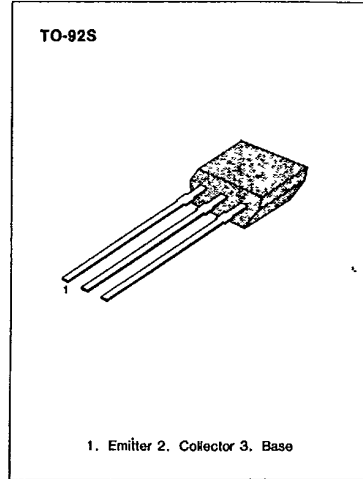
T-29-17

LOW FREQUENCY AMPLIFIER

- Complement to KSC2785
- Collector-Base Voltage $V_{CBO} = -60V$

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ C$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-60	V
Collector-Emitter Voltage	V_{CEO}	-50	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-150	mA
Collector Dissipation	P_C	250	mW
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature	T_{stg}	-55 ~ 150	$^\circ C$

**ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)**

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C = -100\mu A, I_E = 0$	-60			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C = -10mA, I_B = 0$	-50			V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E = -10\mu A, I_C = 0$	-5			V
Collector Cut-off Current	I_{CBO}	$V_{CB} = -60V, I_E = 0$			-0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -5V, I_C = 0$			-0.1	μA
DC Current Gain	h_{FE}	$V_{CE} = -6V, I_C = -1mA$	40		700	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -100mA, I_B = -10mA$		-0.18	-0.3	V
Base-Emitter On Voltage	$V_{BE(on)}$	$V_{CE} = -6V, I_C = -1mA$	-0.50	-0.62	-0.80	V
Current-Gain-Bandwidth Product	f_T	$V_{CE} = -6V, I_C = -10mA$	50	180		MHz
Output Capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0$ $f = 1MHz$		2.8		pF
Noise Figure	NF	$V_{CE} = -6V, I_C = -0.3mA$ $f = 100Hz, R_s = 10K\Omega$		6.0	20	dB

 h_{FE} CLASSIFICATION

Classification	R	O	Y	G	L
h_{FE}	40-80	70-140	120-240	200-400	350-700

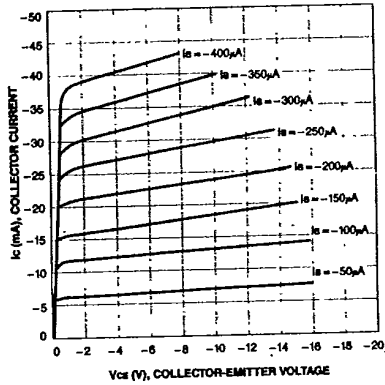


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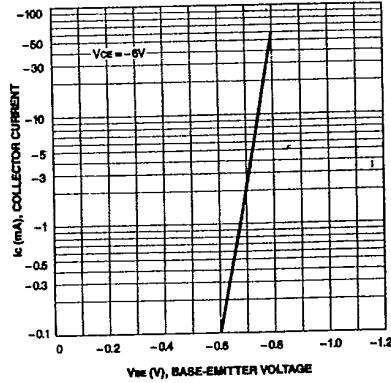
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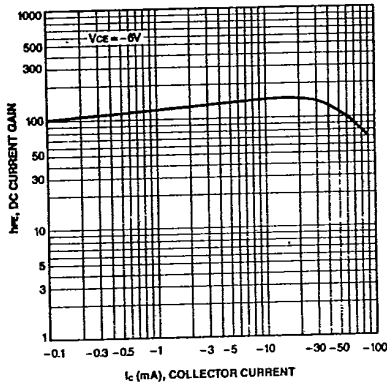
STATIC CHARACTERISTIC



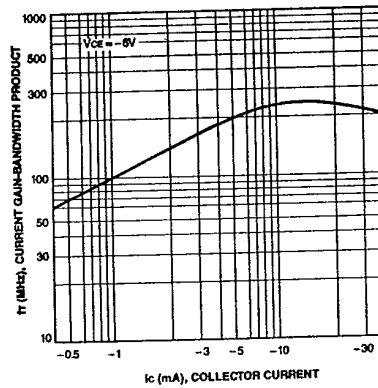
BASE-EMITTER ON VOLTAGE



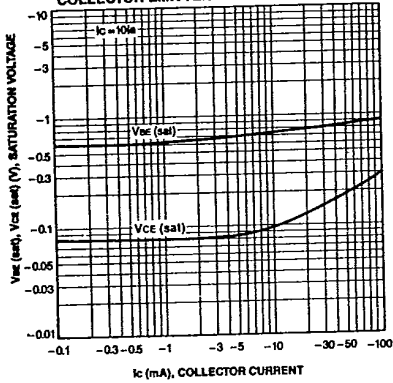
DC CURRENT GAIN



CURRENT GAIN-BANDWIDTH PRODUCT



BASE-EMITTER SATURATION VOLTAGE
COLLECTOR-EMITTER SATURATION VOLTAGE



COLLECTOR OUTPUT CAPACITANCE

